



PHYSIKALISCHES KOLLOQUIUM

Mittwoch, 23.05.2012, um 17:15 Uhr

Ort: Reichenhainer Str. 90; Neues Hörsaalgebäude, Raum: 2/N013



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Terahertz-Spektroskopie von Halbleiter-Nanostrukturen mit dem Freie-Elektronen-Laser

Free electron lasers (FEL) can deliver high-intensity narrow-band radiation in otherwise not easily accessible spectral ranges, such as the THz range.

After briefly introducing the FEL at HZDR, I will discuss a quantum optical experiment, where we use the FEL to drive the 1s-2p intra-excitonic transition in semiconductor quantum wells and observe the so-called Autler-Townes splitting, a manifestation of electronic states dressed by the radiation field [1]. Our results indicate that we enter a regime well beyond the rotating-wave and two-level approximations. As a second example I will discuss pump-probe experiments on multilayer graphene over a wide range of photon energies (10-250 meV), hereby unveiling the relevant electronic relaxation mechanisms [2]. Remarkably we observe a sign change of the probe signal, i.e. a crossover from induced bleaching to induced absorption, which is related to the interplay between inter- and intraband absorption.

[1] M. Wagner, H. Schneider, D. Stehr, S. Winnerl, A. M. Andrews, S. Schartner, G. Strasser, M. Helm: „Observation of the intra-exciton Autler-Townes effect in GaAs/AlGaAs semiconductor quantum wells”, Phys. Rev. Lett. 105, 167401 (2010)

[2] S. Winnerl, M. Orlita, P. Plochocka, P. Kossacki, M. Potemski, T. Winzer, E. Malic, A. Knorr, M. Sprinkle, C. Berger, W. A. de Heer, H. Schneider, M. Helm: "Carrier relaxation in epitaxial graphene photoexcited near the Dirac point", Phys. Rev. Lett. 107, 237401 (2011)

Alle Zuhörer sind ab 17.00 zum Kaffee vor dem Hörsaal eingeladen.

Informationen zum Vortrag erteilt Prof. Rudolf Bratschitsch, Tel. 0371/531 39182